BAS16DXV6

Dual Switching Diode

Features

- S Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC−Q101 Qualified and PPAP Capable
- These Devices are Pb−Free, Halogen Free/BFR Free and are RoHS Compliant

ON Semiconductor®

SOT−563
CASE 463A
PLASTIC

MARKING DIAGRAM

A6 = Specific Device Code
M = Date Code
▪ = Pb−Free Package
(Note: Microdot may be in either location)

MAXIMUM RATINGS (T_A = 25°C)

Rating	Symbol	Max	Unit
Continuous Reverse Voltage	V_R	100	V
Recurrent Peak Forward Current	I_F	200	mA
Peak Forward Surge Current Pulse Width = 10 μs	$I_{FM(surge)}$	500	mA

THERMAL CHARACTERISTICS

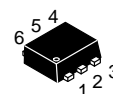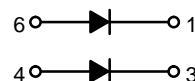| Characteristic (One Junction Heated)	Symbol	Max	Unit
Total Device Dissipation (Note 1) T_A = 25°C Derate above 25°C	P_D	357 2.9	mW mW/°C
Thermal Resistance, Junction-to-Ambient (Note 1)	$R_{\theta JA}$	350	°C/W
Characteristic (Both Junctions Heated)	**Symbol**	**Max**	**Unit**
Total Device Dissipation (Note 1) T_A = 25°C Derate above 25°C	P_D	500 4.0	mW mW/°C
Thermal Resistance, Junction-to-Ambient (Note 1)	$R_{\theta JA}$	250	°C/W
Junction and Storage Temperature	T_J, T_{stg}	−55 to +150	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.
1. FR−4 @ Minimum Pad

ORDERING INFORMATION

Device	Package	Shipping[†]
BAS16DXV6T1G	SOT−563 (Pb−Free)	4000 / Tape & Reel
SBAS16DXV6T1G	SOT−563 (Pb−Free)	4000 / Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification Brochure, BRD8011/D.

BAS16DXV6

ELECTRICAL CHARACTERISTICS ($T_A = 25°C$ unless otherwise noted)

Characteristic	Symbol	Min	Max	Unit
Forward Voltage ($I_F = 1.0$ mA) ($I_F = 10$ mA) ($I_F = 50$ mA) ($I_F = 150$ mA)	V_F	– – – –	715 855 1000 1250	mV
Reverse Current ($V_R = 100$ V) ($V_R = 75$ V, $T_J = 150°C$) ($V_R = 25$ V, $T_J = 150°C$)	I_R	– – –	1.0 50 30	µA
Capacitance ($V_R = 0$, f = 1.0 MHz)	C_D	–	2.0	pF
Reverse Recovery Time ($I_F = I_R = 10$ mA, $R_L = 50 \Omega$) (Figure 1)	t_{rr}	–	6.0	ns
Stored Charge ($I_F = 10$ mA to $V_R = 6.0$ V, $R_L = 500 \Omega$) (Figure 2)	QS	–	45	PC
Forward Recovery Voltage ($I_F = 10$ mA, $t_r = 20$ ns) (Figure 3)	V_{FR}	–	1.75	V

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

BAS16DXV6
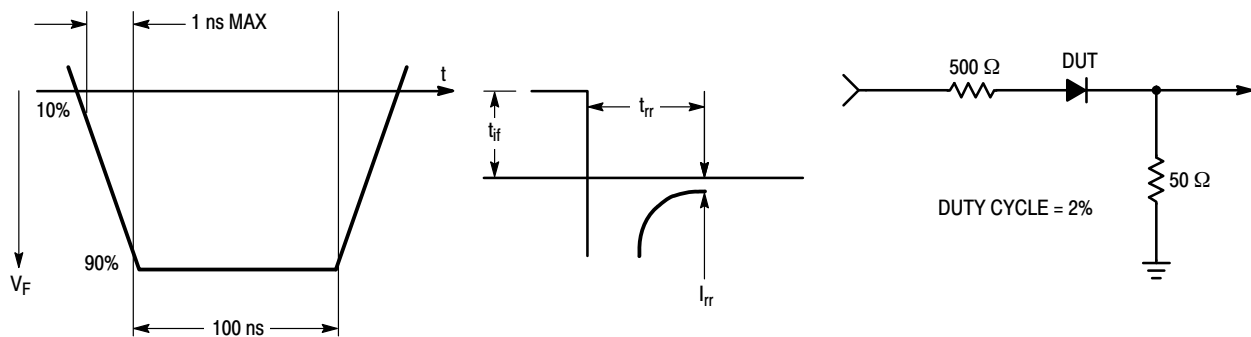
Figure 1. Reverse Recovery Time Equivalent Test Circuit

$$V_{CM} = \frac{Qa}{C}$$
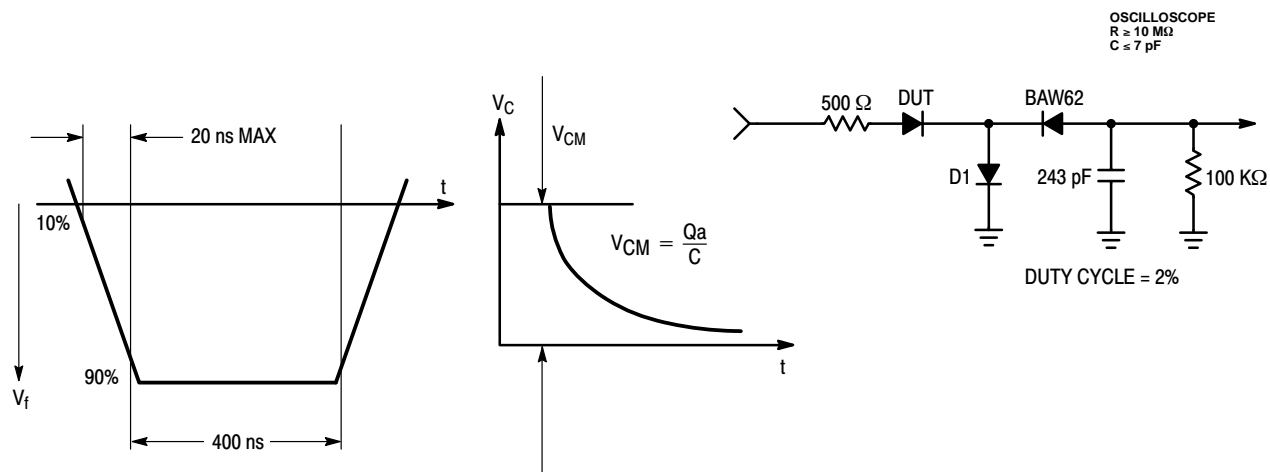
Figure 2. Stored Charge Equivalent Test Circuit
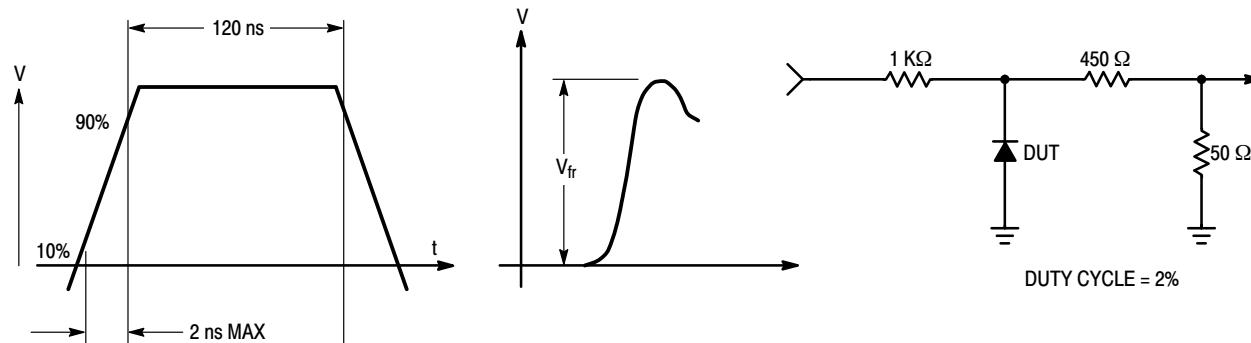
Figure 3. Forward Recovery Voltage Equivalent Test Circuit
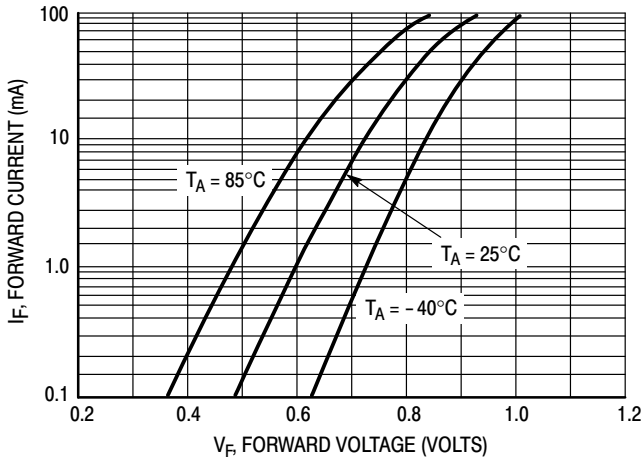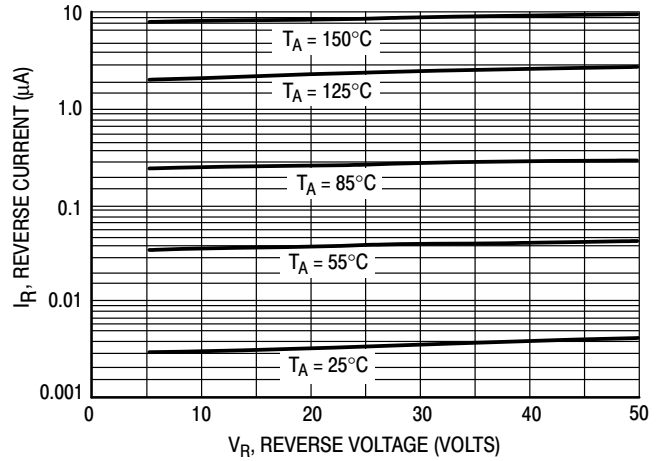
BAS16DXV6

TYPICAL CHARACTERISTICS

Figure 4. Forward Voltage
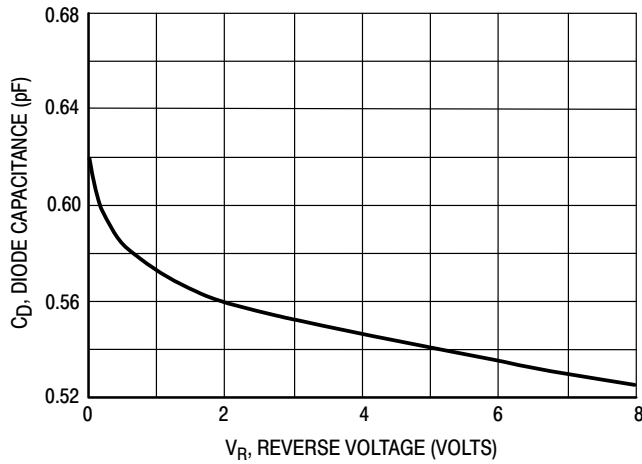

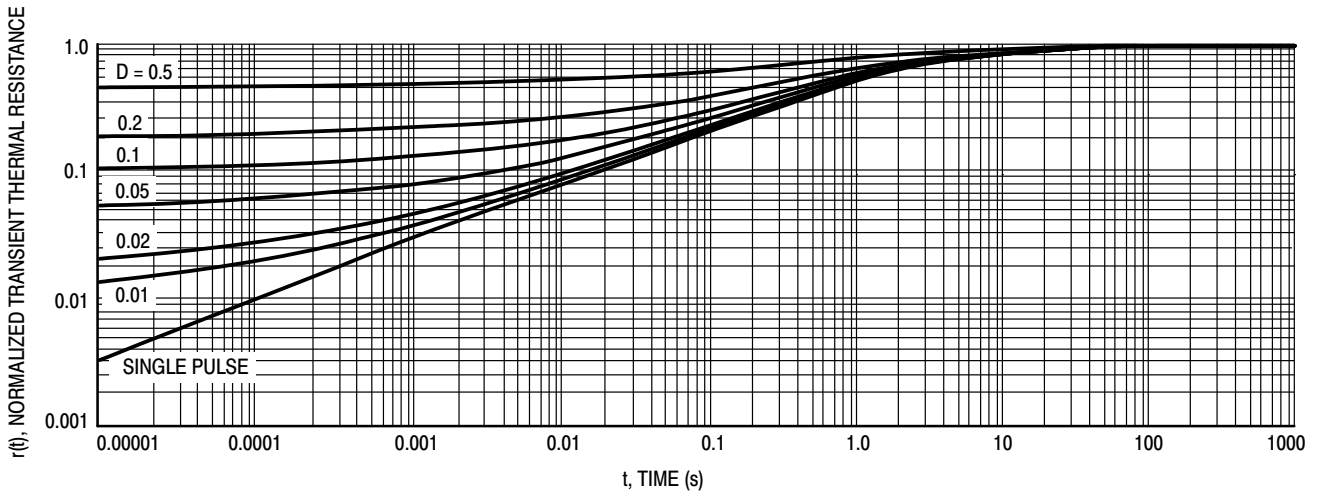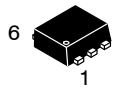
Figure 5. Leakage Current

Figure 6. Capacitance

Figure 7. Normalized Thermal Response

SOT−563, 6 LEAD
CASE 463A
ISSUE H

DATE 26 JAN 2021

6
1

SCALE 4:1

NOTES:
1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 2009.
2. CONTROLLING DIMENSION: MILLIMETERS
3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH THICKNESS. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL.

PIN ONE INDICATOR

6X L

H_E

6X b

⊕ | 0.08 Ⓜ | A | B

TOP VIEW

SIDE VIEW

1.30

6X 0.30

6X 0.45

1.80

0.50 PITCH
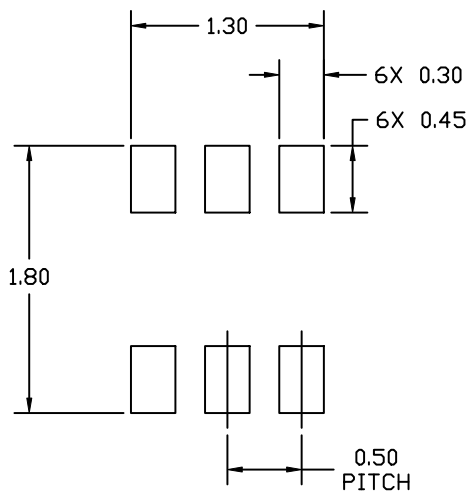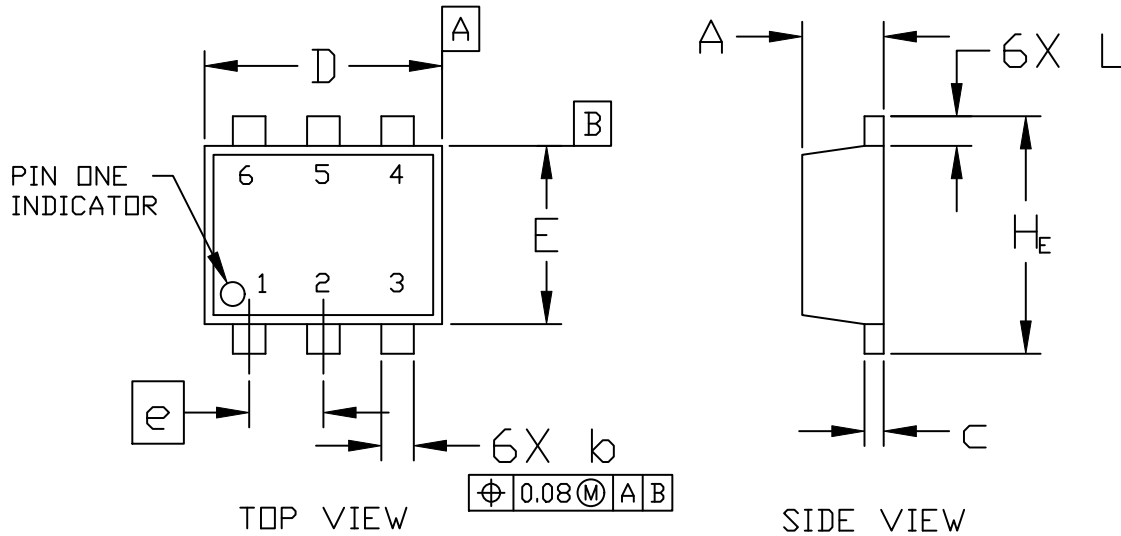
DIM	MILLIMETERS		
	MIN.	NOM.	MAX.
A	0.50	0.55	0.60
b	0.17	0.22	0.27
c	0.08	0.13	0.18
D	1.50	1.60	1.70
E	1.10	1.20	1.30
e	0.50 BSC		
L	0.10	0.20	0.30
H_E	1.50	1.60	1.70

RECOMMENDED MOUNTING FOOTPRINT*

* For additional information on our Pb−Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

DOCUMENT NUMBER:	98AON11126D		
DESCRIPTION:	SOT−563, 6 LEAD		PAGE 1 OF 2

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STYLE 1:
PIN 1. EMITTER 1
    2. BASE 1
    3. COLLECTOR 2
    4. EMITTER 2
    5. BASE 2
    6. COLLECTOR 1

STYLE 2:
PIN 1. EMITTER 1
    2. EMITTER 2
    3. BASE 2
    4. COLLECTOR 2
    5. BASE 1
    6. COLLECTOR 1

STYLE 3:
PIN 1. CATHODE 1
    2. CATHODE 1
    3. ANODE/ANODE 2
    4. CATHODE 2
    5. CATHODE 2
    6. ANODE/ANODE 1

STYLE 4:
PIN 1. COLLECTOR
    2. COLLECTOR
    3. BASE
    4. EMITTER
    5. COLLECTOR
    6. COLLECTOR

STYLE 5:
PIN 1. CATHODE
    2. CATHODE
    3. ANODE
    4. ANODE
    5. CATHODE
    6. CATHODE

STYLE 6:
PIN 1. CATHODE
    2. ANODE
    3. CATHODE
    4. CATHODE
    5. CATHODE
    6. CATHODE

STYLE 7:
PIN 1. CATHODE
    2. ANODE
    3. CATHODE
    4. CATHODE
    5. ANODE
    6. CATHODE

STYLE 8:
PIN 1. DRAIN
    2. DRAIN
    3. GATE
    4. SOURCE
    5. DRAIN
    6. DRAIN

STYLE 9:
PIN 1. SOURCE 1
    2. GATE 1
    3. DRAIN 2
    4. SOURCE 2
    5. GATE 2
    6. DRAIN 1

STYLE 10:
PIN 1. CATHODE 1
    2. N/C
    3. CATHODE 2
    4. ANODE 2
    5. N/C
    6. ANODE 1

STYLE 11:
PIN 1. EMITTER 2
    2. BASE 2
    3. COLLECTOR 1
    4. EMITTER 1
    5. BASE 1
    6. COLLECTOR 2

**GENERIC
MARKING DIAGRAM***
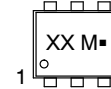
XX = Specific Device Code
M = Month Code
▪ = Pb−Free Package

*This information is generic. Please refer to
device data sheet for actual part marking.
Pb−Free indicator, "G" or microdot "▪", may
or may not be present. Some products may
not follow the Generic Marking.

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PUBLICATION ORDERING INFORMATION

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